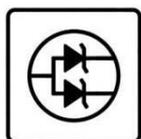


# MSKSEMI 美森科

SEMICONDUCTOR



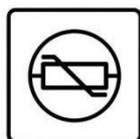
ESD



TVS



TSS



MOV



GDT

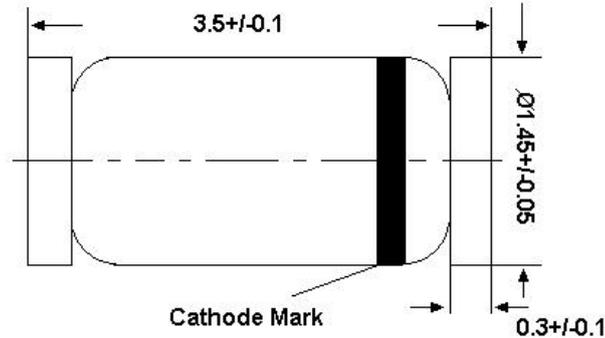


PLED

## LLDB3/LLDB4

Product specification

These diacs are intended for use in thyristor phase control, circuits for lamp-dimming, universal-motor speed controls, and heat controls.



**Glass case MiniMELF**  
**Dimensions in mm**  
**LL-34**

**REEL SPECIFICATION**

P/N	PKG	QTY
LLDB3/LLDB4	LL-34	2500

**Absolute Maximum Ratings (Ta = 25°C)**

Parameter	Symbol	Value	Unit
Power Dissipation (Ta = 65 °C)	P <sub>tot</sub>	150	mW
Repetitive Peak On-state Current (tp = 20 µs, f = 100 Hz)	I <sub>TRM</sub>	2	A
Operating Junction and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	- 40 to + 125	°C

**Characteristics at Ta = 25°C)**

Parameter	Symbol	Min.	Max.	Unit
Breakover Voltage at C = 22 nF, see diagram 1	V <sub>BO</sub>	28	36	V
		35	45	
Breakover Voltage Symmetry at C = 22 nF, see diagram 1	[ +V <sub>BO</sub>  - -V <sub>BO</sub>  ]	-	3	V
Dynamic Breakover Voltage at ΔI = [I <sub>BO</sub> to I <sub>F</sub> = 10 mA]	ΔV ±	5	-	V
Output Voltage See diagram 2	V <sub>O</sub>	5	-	V
Breakover Current at C = 22 nF	I <sub>BO</sub>	-	50	µA
Leakage Current at V <sub>B</sub> = 0.5 V <sub>BO</sub> max	I <sub>B</sub>	-	10	µA
Rise Time See diagram 3	t <sub>r</sub>	-	2	µs

Diagram 1: Current-voltage characteristics

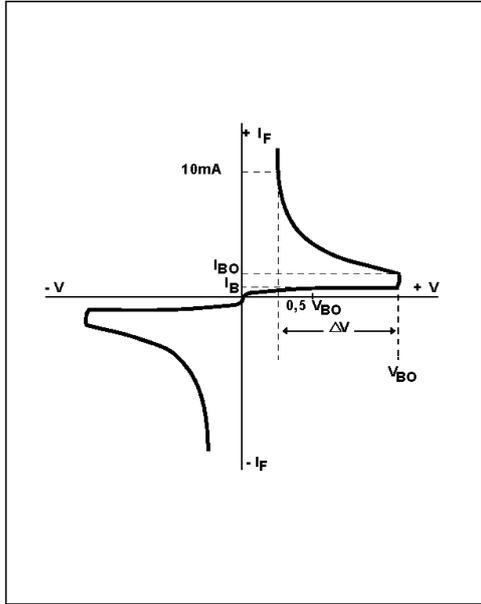


Diagram 2: Test circuit for output voltage

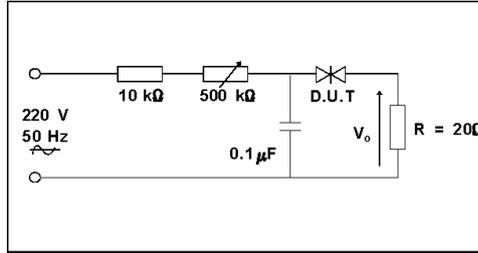


Diagram 3: Test circuit see diagram 2. Adjust R for  $I_p = 0.5A$

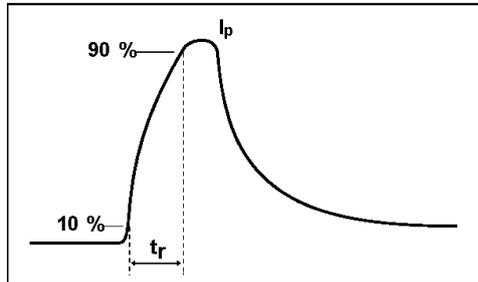


Fig. 1: Power dissipation versus ambient temperature (maximum values)

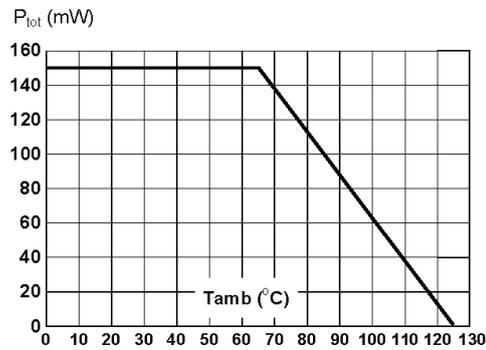


Fig. 2: Relative variation of  $V_{BO}$  versus junction temperature (typical values)

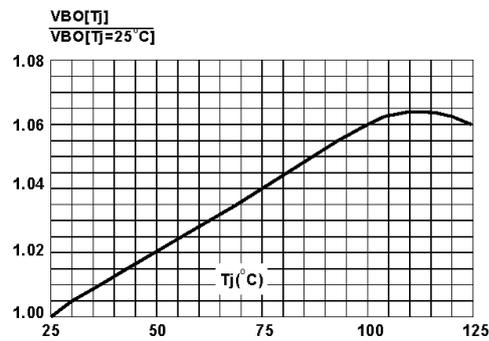
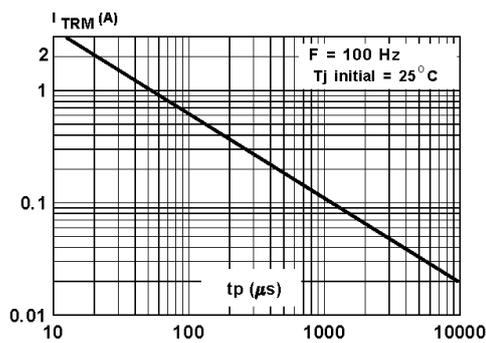


Fig. 3: Peak pulse current versus pulse duration (maximum values)



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